



DOCKET NO. SC13207TP

UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT Dharesh Jawarani GROUP ART UNIT: 2891
APPLN. NO.: 10/797,222 EXAMINER: Victor V. Yevsikov
FILED: March 10, 2004 CONFIRMATION No.: 4099
TITLE: METHOD OF INHIBITING METAL SILICIDE
ENCROACHMENT IN A TRANSISTOR

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Signature

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Printed Name of Person Signing Certificate

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This paper is filed contemporaneous with the filing of the issue fee for this application. Entrance of the comments provided below regarding the statement of reasons for allowance provided by the Examiner is respectfully requested.

FEES

Applicants authorize the charging of Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any fees owed in connection with this application, or credit Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any refunds.



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REMARKS

In a communication mailed March 20, 2006, claims 1-28 were allowed. The Examiner provided a statement of reasons for allowance of the claims which Applicants believe is overly focused on one single claim recital. Applicants are submitting these comments in supplement of the reasons for allowance. The claim language which has been allowed recites novel features than the recited one of "implanting encroachment inhibiting ions into the transistor after selectively removing the unsilicided portions of the metal layer". For example, the prior art made of record does not teach the combination of annealing and material removal in combination with the use of inhibiting ions as recited in each of the independent claims. Further, Applicant submits that other unreferenced dependent claim features are also novel when combined with the whole of the claim limitations.

SEND CORRESPONDENCE TO:

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Respectfully submitted,

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LAW DEPARTMENT
FREESCALE SEMICONDUCTOR, INC.

DATE: March 30, 2006

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Class: 438-592000

ALL ITEMS MARKED WITH AN "X" ARE INCLUDED:

1.	x	1 page Facsimile Cover Sheet
2.	x	1 page PTOL-85B Issue Fee Transmittal (in duplicate)
3.	X	2 page Comments on Statement of Reasons for Allowance

Paid by Deposit Account 503079, Freescale Semiconductor, Inc: \$1700

If Applicant has overlooked any additional fees, or if any overpayment has been made, the Commissioner is hereby authorized to credit or debit Deposit Account 503079. Freescale Semiconductor, Inc.

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